PD - 94322

International
IOR Rectifier

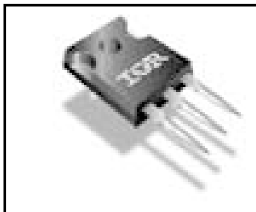
IRFP17N50L

SMPS MOSFET

HEXFET® Power MOSFET

V_{DSS}	$R_{DS(on)}$ typ.	T_{rr} typ.	I_D
500V	0.28Ω	170ns	16A

Applications
- Switch Mode Power Supply (SMPS)
- Zero Voltage Switching (ZVS) and High Frequency Circuit
- Uninterruptible Power Supply
- High Speed Power Switching
- PWM Inverters



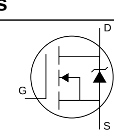
TO-247AC

Benefits
- Low Gate Charge Qg results in Simple Drive Requirement
- Improved Gate, Avalanche and Dynamic dv/dt Ruggedness
- Fully Characterized Capacitance and Avalanche Voltage and Current
- Low Trr and Soft Diode Recovery
- High Performance Optimised Anti-parallel Diode

Absolute Maximum Ratings

	Parameter	Max.	Units
I_D @ T_C = 25°C	Continuous Drain Current, V_{GS} @ 10V	16	A
I_D @ T_C = 100°C	Continuous Drain Current, V_{GS} @ 10V	11	
I_{DM}	Pulsed Drain Current ①	64	
P_D @T_C = 25°C	Power Dissipation	220	W
	Linear Derating Factor	1.8	W/°C
V_{GS}	Gate-to-Source Voltage	± 30	V
dv/dt	Peak Diode Recovery dv/dt ③	13	V/ns
T_J T_{STG}	Operating Junction and Storage Temperature Range	-55 to + 150	°C
	Soldering Temperature, for 10 seconds (1.6mm from case)	300	
	Mounting Torque, 6-32 or M3 screw	10	lbf.in(N.m)

Diode Characteristics

Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
I_S	Continuous Source Current (Body Diode)	——	——	16	A	MOSFET symbol showing the integral reverse p-n junction diode. 
I_{SM}	Pulsed Source Current (Body Diode) ①	——	——	64		
V_{SD}	Diode Forward Voltage	——	——	1.5	V	T_J = 25°C, I_S = 16A, V_{GS} = 0V ④
t_{rr}	Reverse Recovery Time	——	170	250	ns	T_J = 25°C I_F = 16A
		——	220	330		T_J = 125°C di/dt = 100A/µs ④
Q_{rr}	Reverse Recovery Charge	——	470	710	nC	T_J = 25°C
		——	810	1210		T_J = 125°C
I_{RRM}	Reverse Recovery Current	——	7.3	11	A	
t_{on}	Forward Turn-On Time	Intrinsic turn-on time is negligible (turn-on is dominated by L_S+L_D)				

09/20/01

Static @ T_J = 25°C (unless otherwise specified)

Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)DSS}$	Drain-to-Source Breakdown Voltage	500	——	——	V	V_{GS} = 0V, I_D = 250µA
$\Delta V_{(BR)DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	——	0.6	——	V/°C	Reference to 25°C, I_D = 1mA⑥
$R_{DS(on)}$	Static Drain-to-Source On-Resistance	——	0.28	0.32	Ω	V_{GS} = 10V, I_D = 9.9A ④
$V_{GS(th)}$	Gate Threshold Voltage	3.0	——	5.0	V	V_{DS} = V_{GS}, I_D = 250µA
I_{DSS}	Drain-to-Source Leakage Current	——	——	50	µA	V_{DS} = 500V, V_{GS} = 0V
		——	——	2.0	mA	V_{DS} = 400V, V_{GS} = 0V, T_J = 125°C
I_{GSS}	Gate-to-Source Forward Leakage	——	——	100	nA	V_{GS} = 30V
	Gate-to-Source Reverse Leakage	——	——	-100		V_{GS} = -30V

Dynamic @ T_J = 25°C (unless otherwise specified)

Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
g_{fs}	Forward Transconductance	11	——	——	S	V_{DS} = 50V, I_D = 9.9A
Q_g	Total Gate Charge	——	——	130	nC	I_D = 16A
Q_{gs}	Gate-to-Source Charge	——	——	33		V_{DS} = 400V
Q_{gd}	Gate-to-Drain ("Miller") Charge	——	——	59		V_{GS} = 10V ④
$t_{d(on)}$	Turn-On Delay Time	——	21	——	ns	V_{DD} = 250V
t_r	Rise Time	——	51	——		I_D = 16A
$t_{d(off)}$	Turn-Off Delay Time	——	50	——		R_G = 7.5Ω
t_f	Fall Time	——	28	——		V_{GS} = 10V ④
C_{iss}	Input Capacitance	——	2760	——	pF	V_{GS} = 0V
C_{oss}	Output Capacitance	——	325	——		V_{DS} = 25V
C_{rss}	Reverse Transfer Capacitance	——	37	——		ƒ = 1.0MHz
C_{oss}	Output Capacitance	——	3690	——		V_{GS} = 0V, V_{DS} = 1.0V, ƒ = 1.0MHz
C_{oss}	Output Capacitance	——	84	——		V_{GS} = 0V, V_{DS} = 400V, ƒ = 1.0MHz
C_{oss} eff.	Effective Output Capacitance	——	159	——		V_{GS} = 0V, V_{DS} = 0V to 400V ⑤

Avalanche Characteristics

Symbol	Parameter	Typ.	Max.	Units
E_{AS}	Single Pulse Avalanche Energy②	——	390	mJ
I_{AR}	Avalanche Current①	——	16	A
E_{AR}	Repetitive Avalanche Energy①	——	22	mJ

Thermal Resistance

Symbol	Parameter	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case	——	0.56	°C/W
$R_{\theta CS}$	Case-to-Sink, Flat, Greased Surface	0.50	——	
$R_{\theta JA}$	Junction-to-Ambient	——	62	

Notes:

① Repetitive rating; pulse width limited by max. junction temperature.

② Starting T_J = 25°C, L = 3.0mH, R_G = 25Ω, I_{AS} = 16A.

③ $I_{SD} \leq$ 16A, di/dt ≤ 347A/µs, $V_{DD} \leq V_{(BR)DSS}$, $T_J \leq$ 150°C

④ Pulse width ≤ 300µs; duty cycle ≤ 2%.

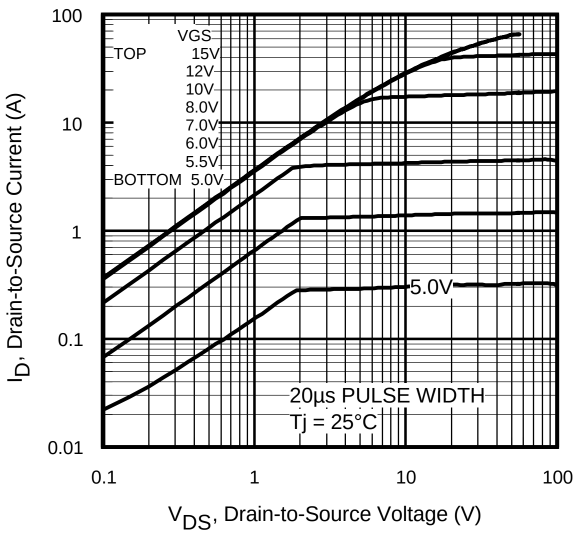


Fig 1. Typical Output Characteristics

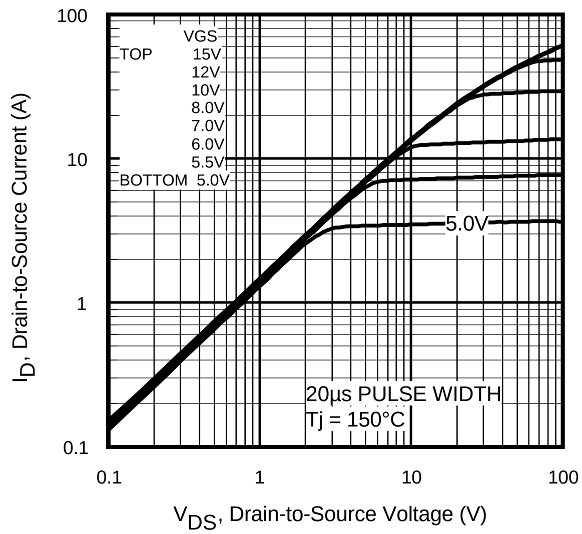


Fig 2. Typical Output Characteristics

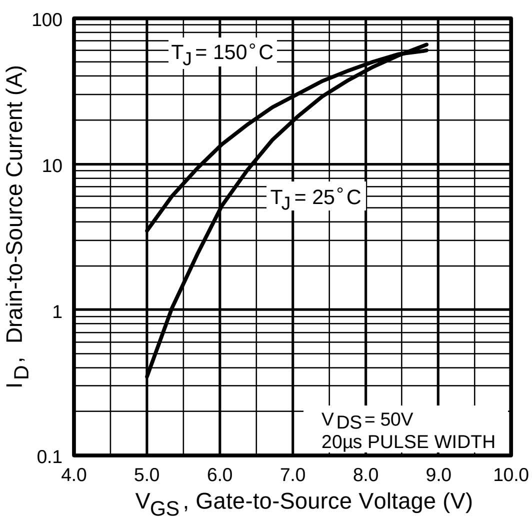


Fig 3. Typical Transfer Characteristics

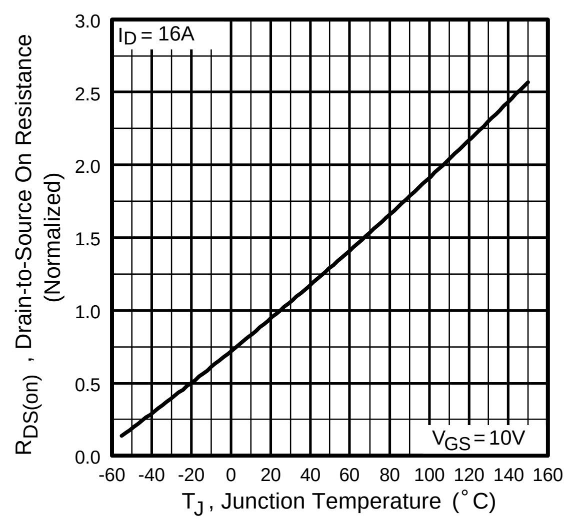


Fig 4. Normalized On-Resistance Vs. Temperature

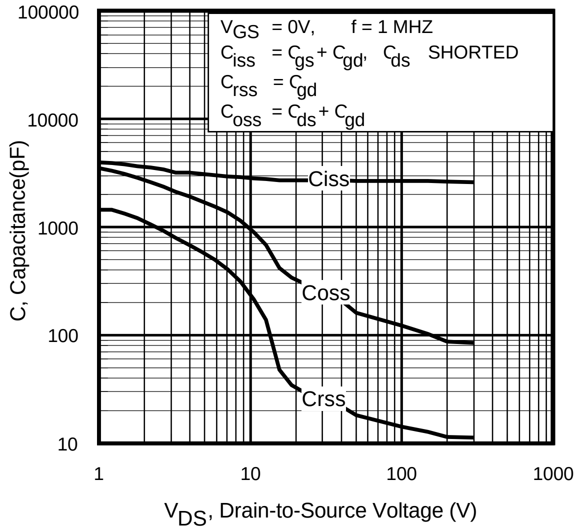


Fig 5. Typical Capacitance Vs. Drain-to-Source Voltage

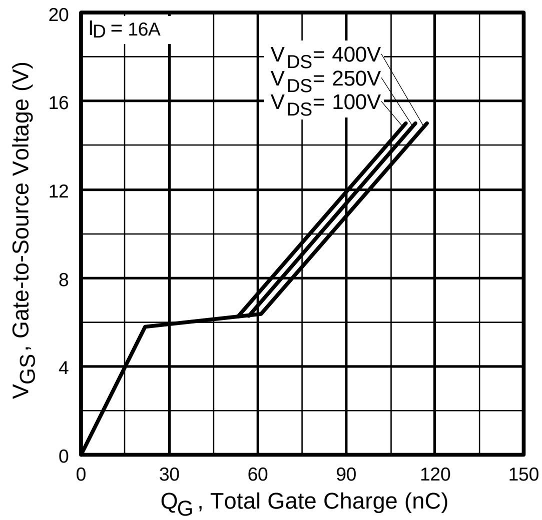


Fig 6. Typical Gate Charge Vs. Gate-to-Source Voltage

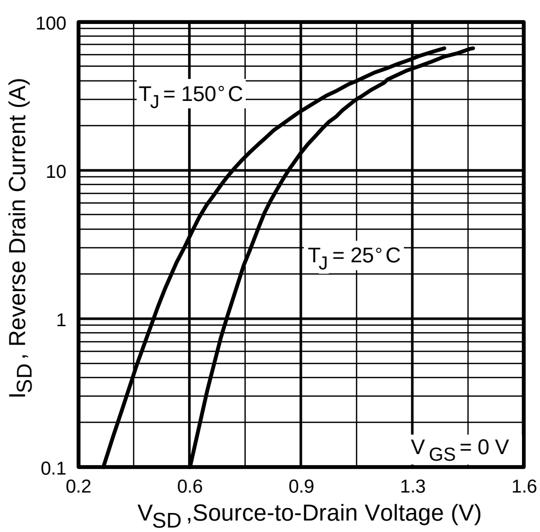


Fig 7. Typical Source-Drain Diode Forward Voltage

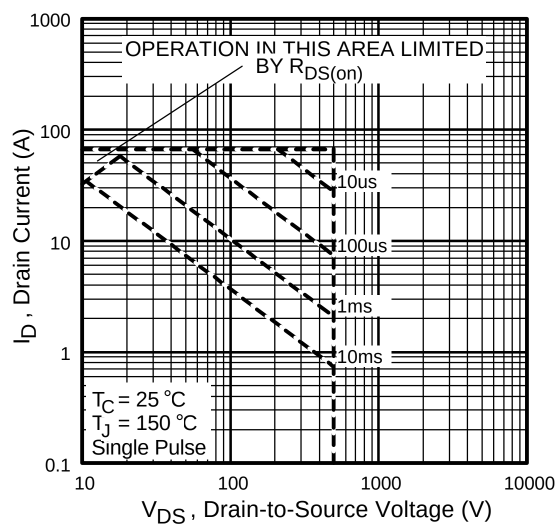


Fig 8. Maximum Safe Operating Area

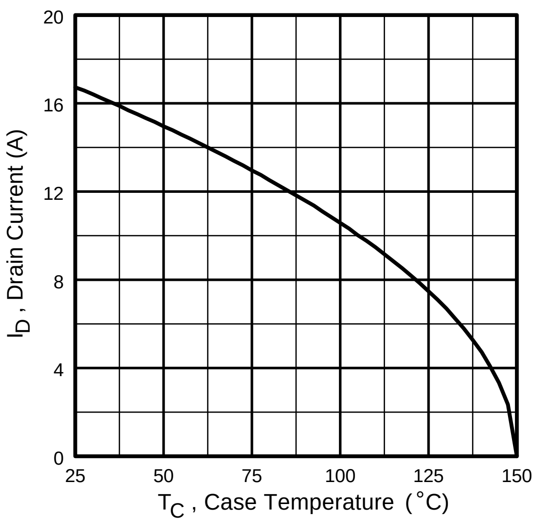


Fig 9. Maximum Drain Current Vs. Case Temperature

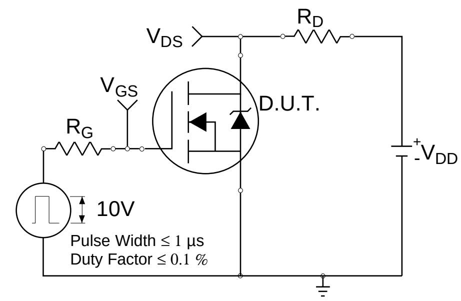


Fig 10a. Switching Time Test Circuit

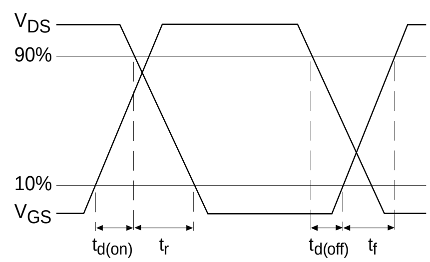


Fig 10b. Switching Time Waveforms

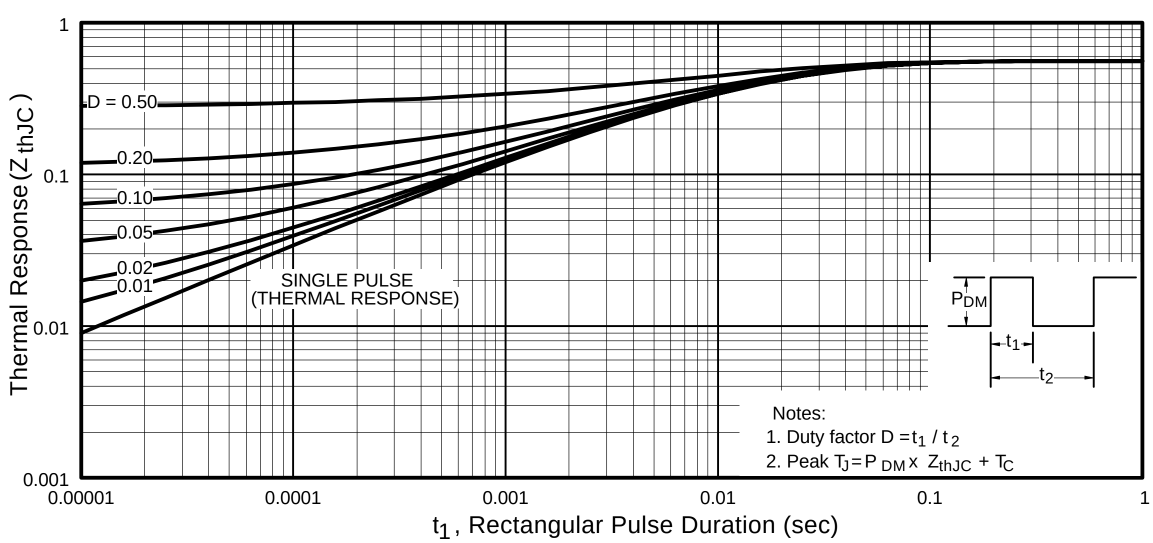


Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Case

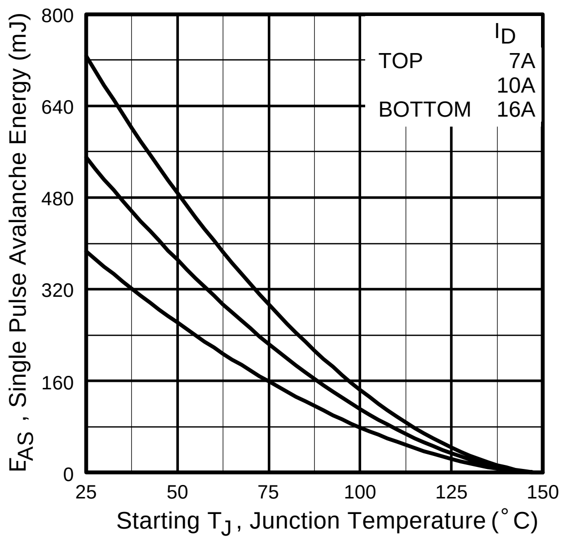


Fig 12a. Maximum Avalanche Energy Vs. Drain Current

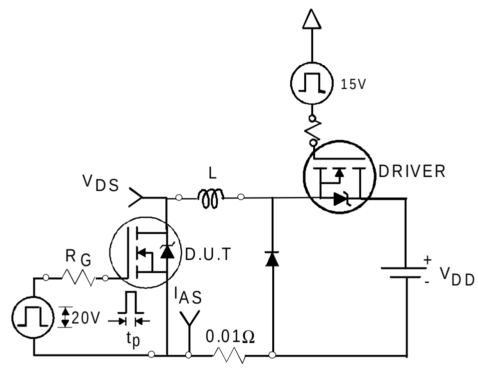


Fig 12c. Unclamped Inductive Test Circuit

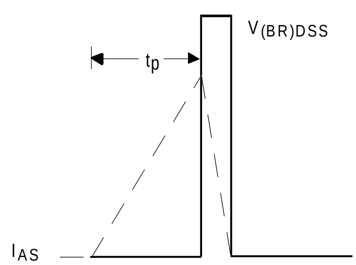


Fig 12d. Unclamped Inductive Waveforms

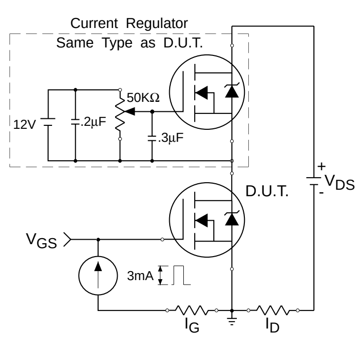


Fig 13a. Gate Charge Test Circuit

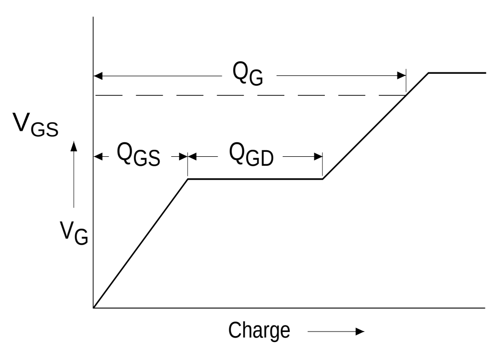
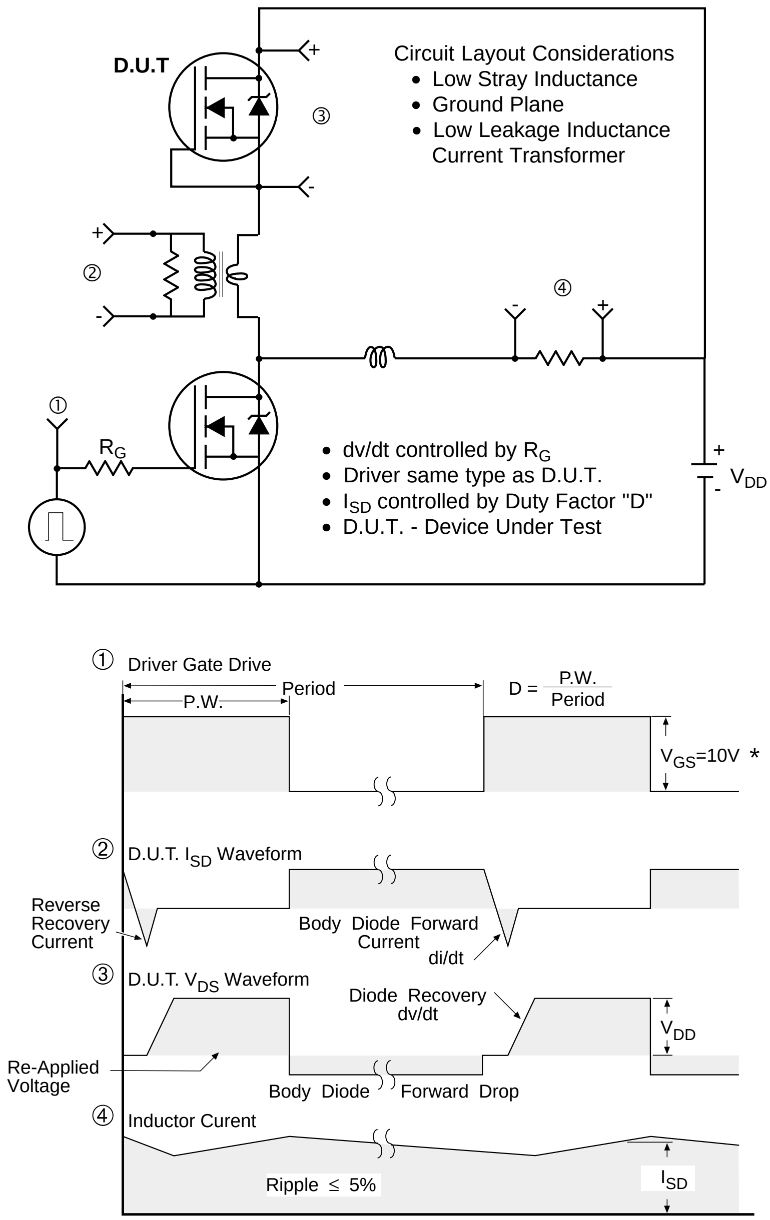


Fig 13b. Basic Gate Charge Waveform

Peak Diode Recovery dv/dt Test Circuit

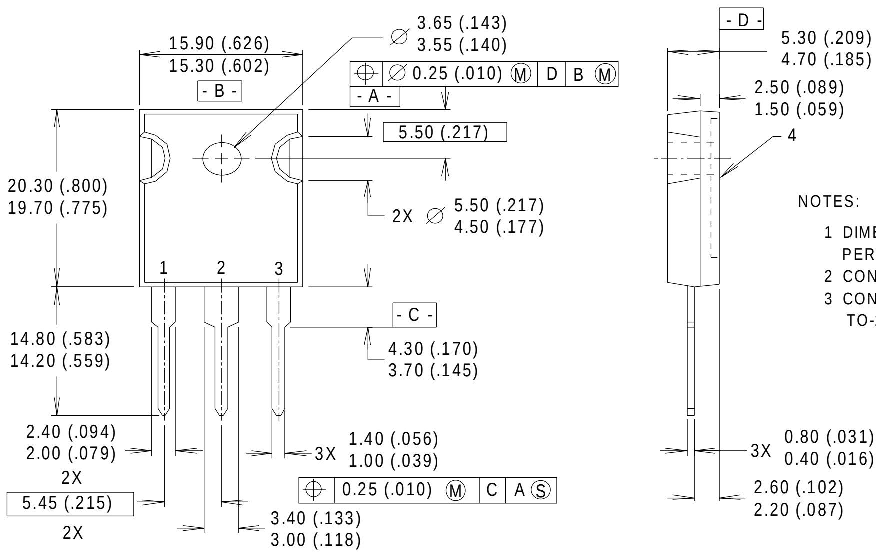


* V_{GS} = 5V for Logic Level Devices

Fig 14. For N-Channel HEXFET® Power MOSFETs

TO - 247 Package Outline

Dimensions are shown in millimeters (inches)



NOTES:

1 DIMENSIONING & TOLERANCING PER ANSI Y14.5M, 1982.
2 CONTROLLING DIMENSION : INCH.
3 CONFORMS TO JEDEC OUTLINE TO-247-AC.

LEAD ASSIGNMENTS

1 - GATE
2 - DRAIN
3 - SOURCE
4 - DRAIN

Data and specifications subject to change without notice.
This product has been designed and qualified for the Automotive [Q101] market.
Qualification Standards can be found on IR's Web site.

International
IOR Rectifier

IR WORLD HEADQUARTERS: 233 Kansas St., El Segundo, California 90245, USA Tel: (310) 252-7105
TAC Fax: (310) 252-7903
Visit us at www.irf.com for sales contact information.09/01